

www.vishay.com

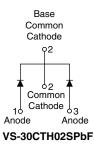
Vishay Semiconductors

Hyperfast Rectifier, 30 A FRED Pt®



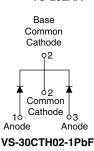


TO-263AB (D²PAK)



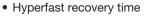


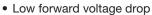
TO-262AA



PRODUCT SUMMARY	PRODUCT SUMMARY						
Package	TO-263AB (D ² PAK), TO-262AA						
I _{F(AV)}	2 x 15 A						
V_{R}	200 V						
V _F at I _F	0.78 V						
t _{rr} typ.	30 ns						
T _J max.	175 °C						
Diode variation	Common cathode						

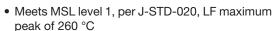
FEATURES













AEC-Q101 qualified

· Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

Vishay Semiconductors 200 V series are the state of the art hyperfast recovery rectifiers designed optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control. guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Peak repetitive reverse voltage		V_{RRM}		200	V	
Average rectified forward current	per diode	I _E (Δ\Λ	T _C = 159 °C	15		
	per device			30	Α	
Non-repetitive peak surge current		I _{FSM}	T _C = 25 °C	200		
Operating junction and storage ten	nperatures	T _J , T _{Stg}		-65 to +175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	Ι _R = 100 μΑ	200	-	-	V	
Face and allows	V _F	I _F = 15 A	-	0.92	1.05	V	
Forward voltage		I _F = 15 A, T _J = 125 °C	-	0.78	0.85	V	
Poverse leakage ourrent	1	$V_R = V_R$ rated	-	-	10		
Reverse leakage current	I _R	$T_J = 125 ^{\circ}C$, $V_R = V_R$ rated	-	5	300	μΑ	
Junction capacitance	C _T	V _R = 200 V	-	57	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nΗ	



VS-30CTH02SPbF, VS-30CTH02-1PbF

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1 A, dI_F/dt = 5$	$0 \text{ A/}\mu\text{s}, \text{ V}_{\text{R}} = 30 \text{ V}$	1	-	35	
Reverse recovery time	t _{rr}	$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A/}\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	-	30	
neverse recovery time		T _J = 25 °C	$I_F = 15 \text{ A}$ $dI_F/dt = 200 \text{ A/µs}$ $V_R = 160 \text{ V}$	-	26	-	ns
		T _J = 125 °C		-	40	-	
Dook recovery current	I _{RRM}	T _J = 25 °C		-	2.8	-	Α
Peak recovery current		T _J = 125 °C		-	6.0	-	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	37	-	nC
		T _J = 125 °C		-	120	-	IIC IIC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}	-65	-	175	°C	
Thermal resistance, junction to case per diode	R_{thJC}	-	-	1.1	°C/W	
Weight		-	2.0	-	g	
Weight		-	0.07	-	OZ.	
Mounting torque		6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case styleTO-2	63AB (D ² PAK)	30CTH02S		
		Case style TO-262		30CT	H02-1	



www.vishay.com

Vishay Semiconductors

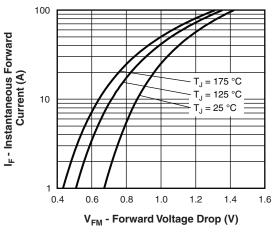


Fig. 1 - Maximum Forward Voltage Drop Characteristics

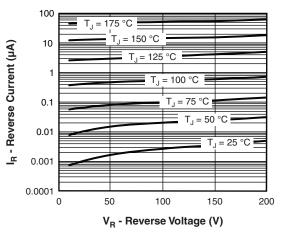


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

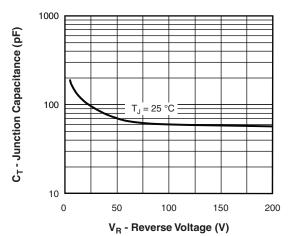


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

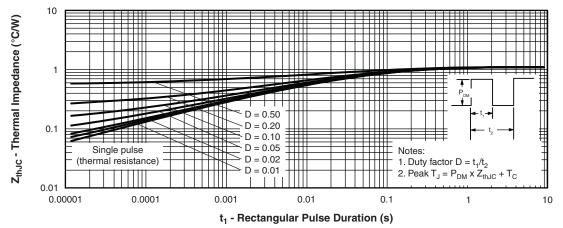


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics





www.vishay.com

Vishay Semiconductors

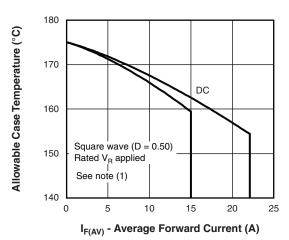


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

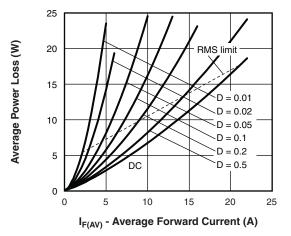


Fig. 6 - Forward Power Loss Characteristics

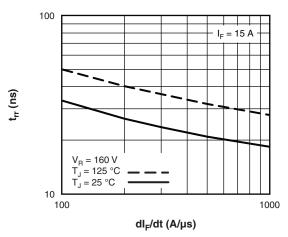


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

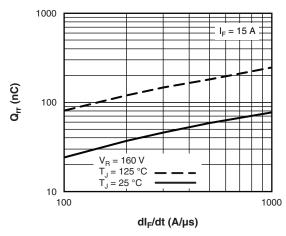


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

(1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; $Pd = Forward power loss = I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); $Pd_{REV} = Inverse power loss = V_{R1} \times I_R (1 - D)$; I_R at $V_{R1} = Rated V_R$

Vishay Semiconductors

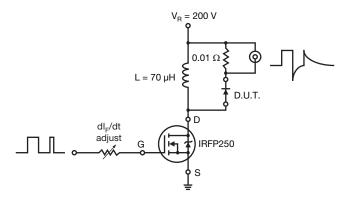
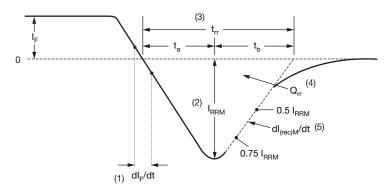


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

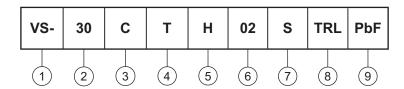
Fig. 10 - Reverse Recovery Waveform and Definitions



Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (30 A)

C = common cathode

 $T = TO-220, D^2PAK$

H = hyperfast rectifier

Voltage rating (02 = 200 V)

7 - • S = D²PAK

• -1 = TO-262

None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D²PAK package)

• TRR = tape and reel (right oriented, for D²PAK package)

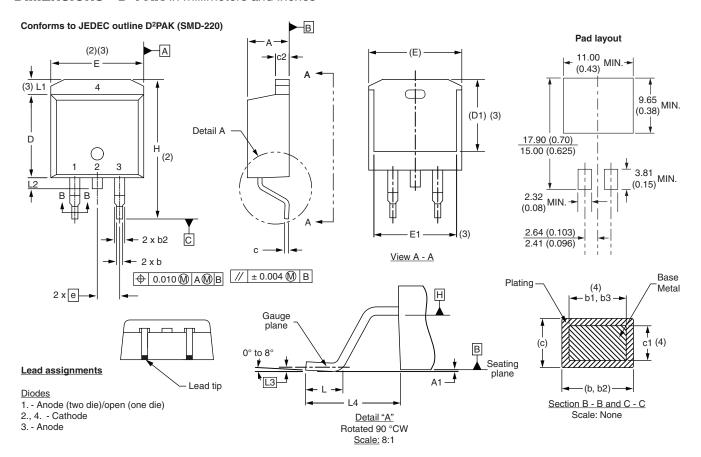
9 - PbF = lead (Pb)-free

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95014				
Part marking information	www.vishay.com/doc?95008				
Packaging information	www.vishay.com/doc?95032				

Vishay Semiconductors

D²**PAK**, **TO**-262

DIMENSIONS - D²PAK in millimeters and inches



SYMBOL	MILLIN	IETERS	INCHES		NOTES	
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIN	IETERS	INC	HES	NOTES	
	MIN.	MAX.	MIN.	MAX.	NOTES	
D1	6.86	8.00	0.270	0.315	3	
E	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54 BSC		0.100 BSC			
Н	14.61	15.88	0.575	0.625		
L	1.78	2.79	0.070	0.110		
L1	-	1.65	-	0.066	3	
L2	1.27	1.78	0.050	0.070		
L3	0.25 BSC		0.010	BSC		
L4	4.78	5.28	0.188	0.208		

Notes

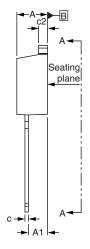
- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- $^{(3)}$ Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch

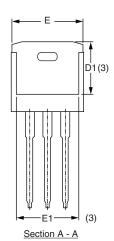
(7) Outline conforms to JEDEC outline TO-263AB

Document Number: 95014 Revision: 31-Mar-09



DIMENSIONS - TO-262 in millimeters and inches





⊕ 0.010 **M** A **M** B

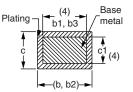
Lead assignments



--3 x b2 --3 x b

<u>Diodes</u>
1. - Anode (two die)/open (one die)
2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

SYMBOL	MILLIMETERS		INC	NOTEO	
	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100) BSC	
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

Notes

- $^{(1)}$ Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches

(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

单击下面可查看定价,库存,交付和生命周期等信息

>>Vishay(威世)